



STP80NF55L-08 STB80NF55L-08 - STB80NF55L-08-1

N-CHANNEL 55V - 0.0065Ω - 80A - TO-220/D²PAK/I²PAK
STripFET™ II POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP80NF55L-08	55 V	0.008Ω	80 A
STB80NF55L-08	55 V	0.008Ω	80 A
STB80NF55L-08-1	55 V	0.008Ω	80 A

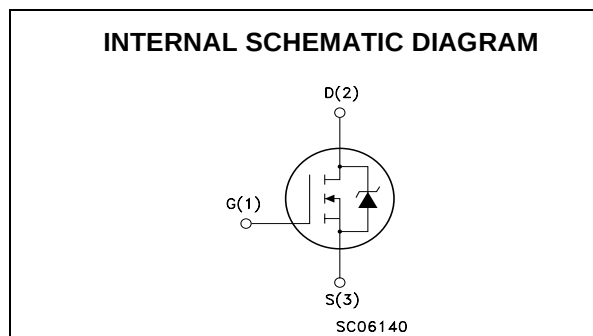
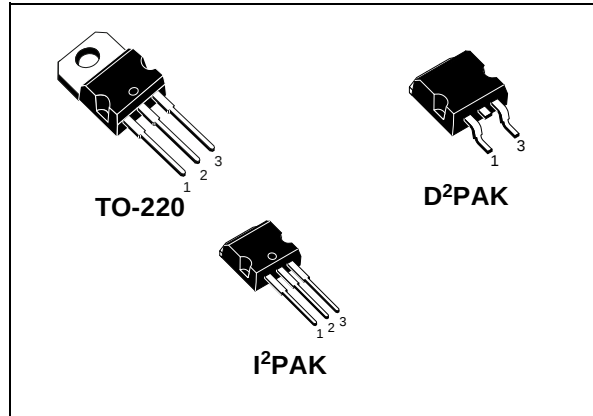
- TYPICAL R_{DS(on)} = 0.0065Ω
- LOW THRESHOLD DRIVE
- LOGIC LEVEL DEVICE

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT SWITCHING APPLICATION



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	55	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	55	V
V _{GS}	Gate- source Voltage	± 16	V
I _D (1)	Drain Current (continuous) at T _C = 25°C	80	A
I _D (1)	Drain Current (continuous) at T _C = 100°C	80	A
I _{DM} (●)	Drain Current (pulsed)	320	A
P _{TOT}	Total Dissipation at T _C = 25°C	300	W
	Derating Factor	2	W/°C
dv/dt (2)	Peak Diode Recovery voltage slope	15	V/ns
E _{AS} (3)	Single Pulse Avalanche Energy	870	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) Current Limited by Package

(2) I_{SD} ≤ 80A, di/dt ≤ 500A/μs, V_{DD} = 40V T_j ≤ T_{JMAX}.

(3) Starting T_j = 25°C, I_D = 40A, V_{DD} = 40V

STP80NF55L-08 - STB80NF55L-08 - STB80NF55L-08-1**THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300	°C

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	55			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 40 A V _{GS} = 5 V, I _D = 40 A		0.0065 0.008	0.008 0.01	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{DS} = 15V, I _D = 40 A		150		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		4350		pF
C _{oss}	Output Capacitance			800		pF
C _{rss}	Reverse Transfer Capacitance			260		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 27V, I_D = 40A$		35		ns
t_r	Rise Time	$R_G = 4.7\Omega, V_{GS} = 4.5V$ (see test circuit, Figure 3)		145		ns
Q_g	Total Gate Charge	$V_{DD} = 27.5V, I_D = 80A,$		75	100	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 4.5V$		20		nC
Q_{gd}	Gate-Drain Charge			30		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 27V, I_D = 40A,$		85		ns
t_f	Fall Time	$R_G = 4.7\Omega, V_{GS} = 4.5V$ (see test circuit, Figure 3)		65		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				320	A
$V_{SD(2)}$	Forward On Voltage	$I_{SD} = 80A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 80A, di/dt = 100A/\mu s,$		85		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 20V, T_J = 150^\circ C$		280		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		6.5		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 2: Unclamped Inductive Waveform

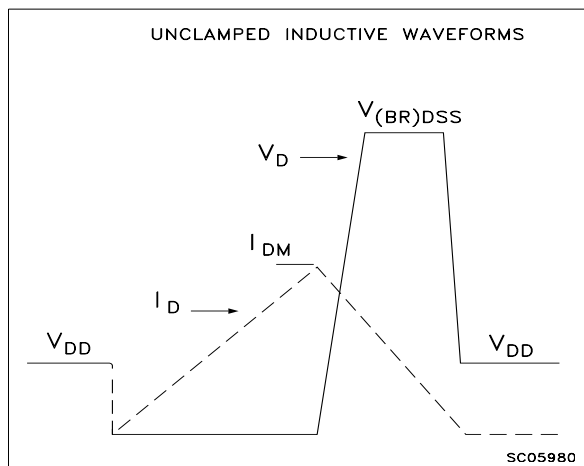
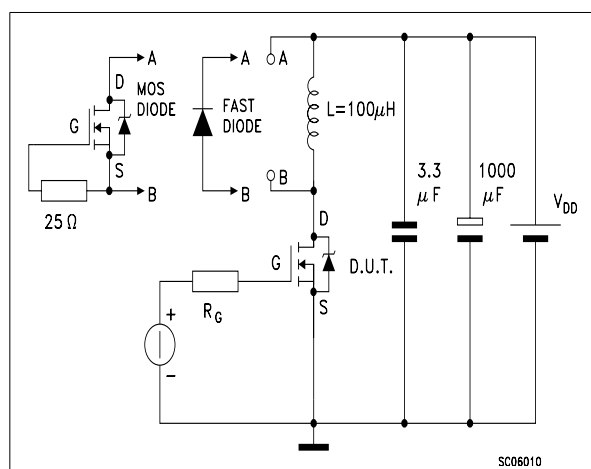
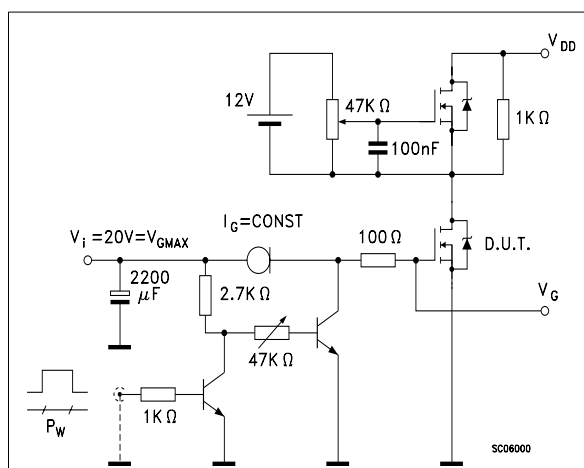
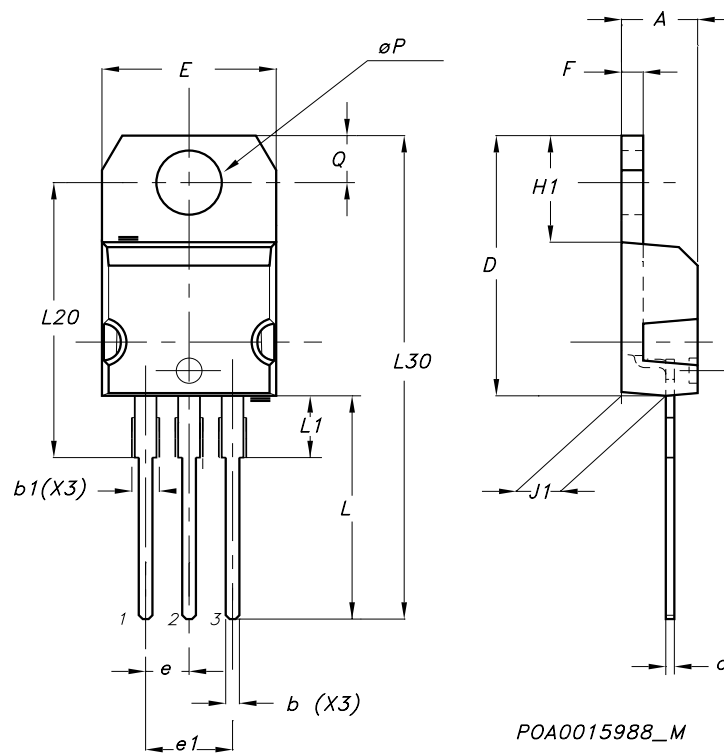


Fig. 4: Gate Charge test Circuit



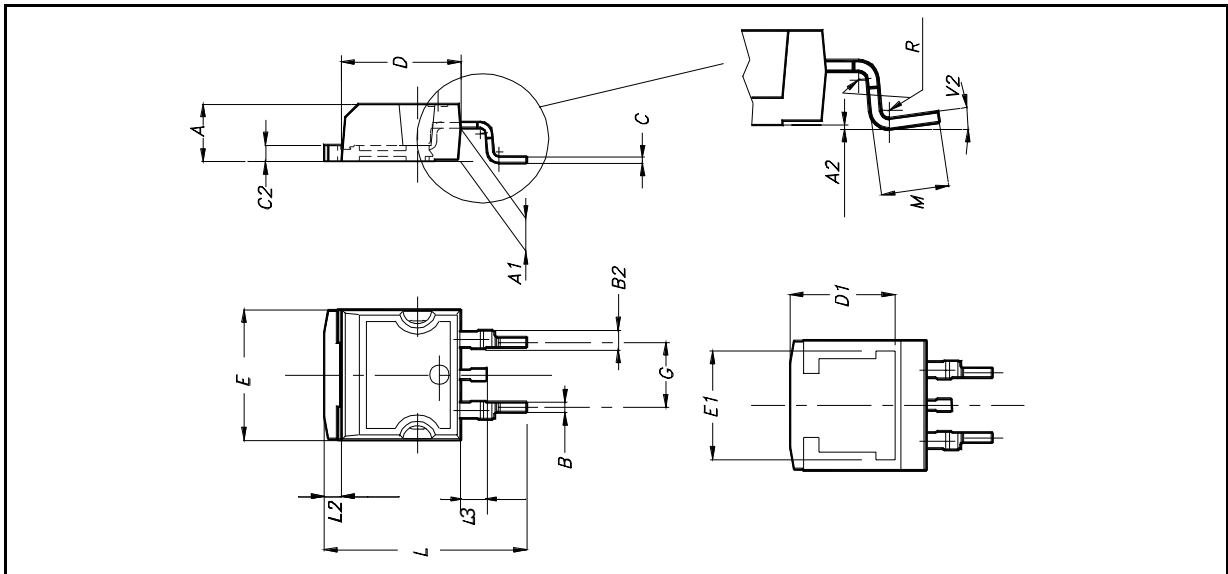
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



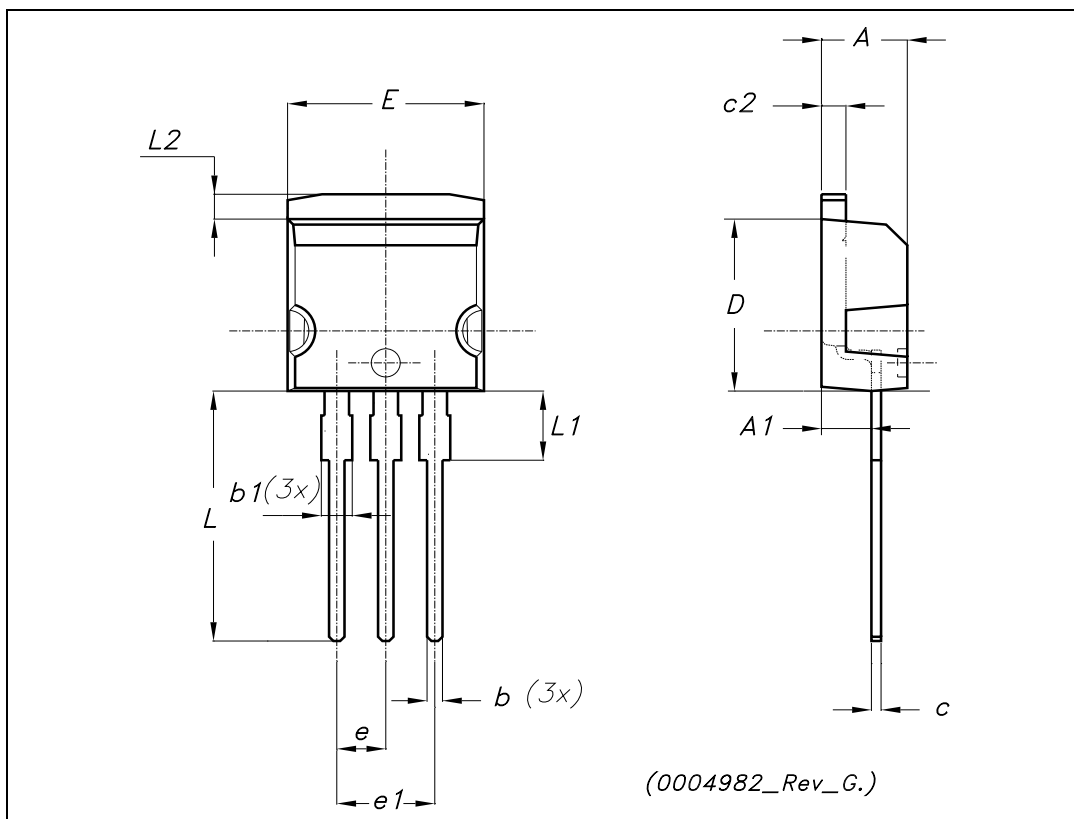
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

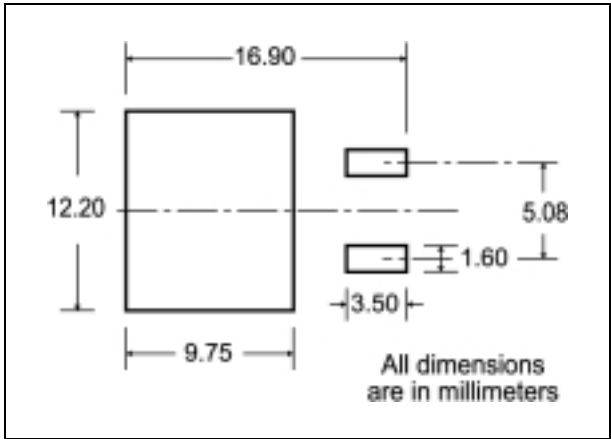


TO-262 (I²PAK) MECHANICAL DATA

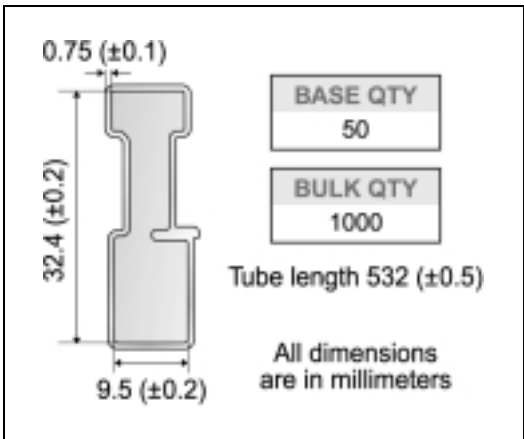
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



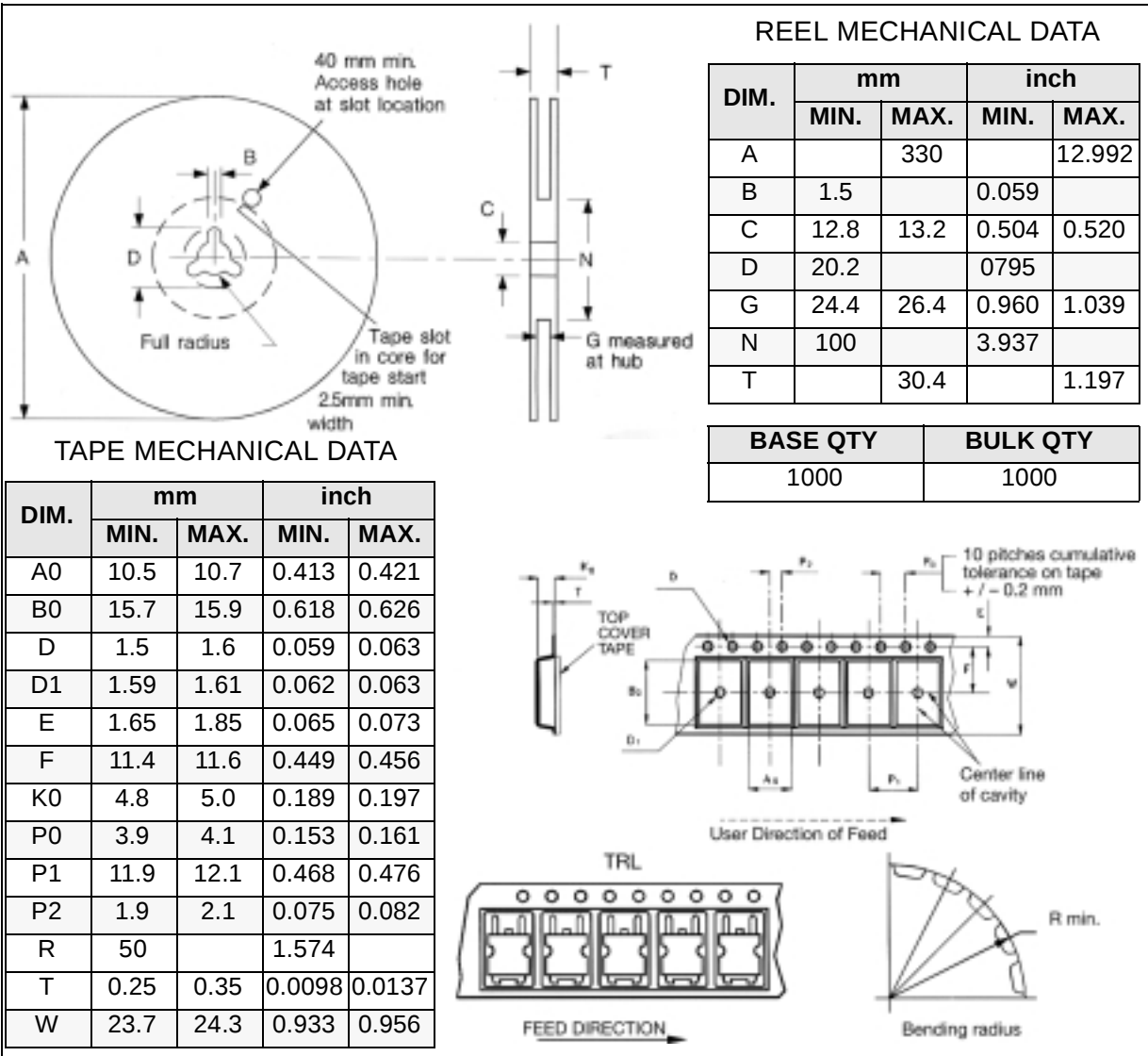
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



* on sales type

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics
All other names are the property of their respective owners

© 2004 STMicroelectronics - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.
<http://www.st.com>